TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (Ultra-High-Speed U-MOSIII)

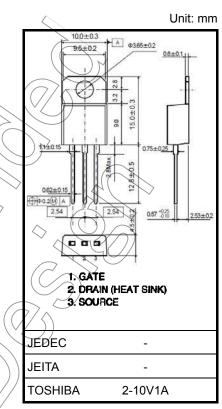
TK60D08J1

Switching Regulator Application

- High-Speed switching
- Small gate charge: Qg = 86 nC (typ.)
- Low drain-source ON resistance: R_{DS (ON)} = 6.2 mΩ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 120 \text{ S}$ (typ.)
- Low leakage current: I_{DSS} = 10 µA (max) (V_{DS} = 75 V)
- Enhancement-mode: V_{th} = 1.1 to 2.3 V (V_{DS} = 10 V, I_D = 1 mA)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics			Symbol	Rating	Uniť
Drain-source voltage			V _{DSS}	75	V.V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)			V _{DGR}	75	Vy I
Gate-source voltage			V _{GSS}	<u></u> ±20	V V
Drain current	DC	(Note 1)	Ι _D	60	Ā
	Pulse	(Note 1)	I _{DP}	240	A
Drain power dissipation (Tc = 25° C)			PD <	140	W
Single pulse avalanche energy (Note 2)			EAS	498	mJ
Avalanche current			IAR) 60	A
Repetitive avalanche energy (Note 3)			EAR	9.2 <	mJ
Channel temperature			Teh	150)°C
Storage temperature range			Tstg	-55 to 450	°C



Weight: 1.35 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	0.89	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	83.3	°C/W

Internal Connection



Note 1: Ensure that the channel & lead temperature does not exceed 150°C.

Note 2: $V_{DD} = 25 \text{ V}, \text{ T}_{ch} = 25^{\circ}\text{C}, \text{ L} = 200 \text{ }\mu\text{H}, \text{ I}_{AR} = 60 \text{ A}, \text{ R}_{G} = 1\Omega$

Note 3: Repetitive rating; pulse width limited by maximum channel temperature.

This transistor is an electrostatic sensitive device. Handle with care.

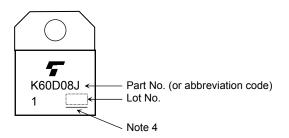
Electrical Characteristics (Ta = 25°C)

Chara	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 16 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$	_		±10	μA
Drain cut-OFF current		I _{DSS}	$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}$	_	—	10	μA
Drain-source breakdown voltage		V (BR) DSS	I_D = 10 mA, V_{GS} = 0 V	75			v
		V (BR) DSX	$I_D = 10 \text{ mA}, \text{ V}_{GS} = -20 \text{ V}$	60		_	
Gate threshold voltage		V _{th}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	(h)/	2.3	V
Drain-source ON resistance		R _{DS (ON)}	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 30 \text{ A}$	2	7.1	9.3	mΩ
			V _{GS} = 10 V, I _D = 30A	H	6.2	7.8	
Forward transfer admittance		Y _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 30 \text{ A}$	60	120		S
Input capacitance		C _{iss}			5450		
Reverse transfer capacitance		C _{rss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$		320	/	pF
Output capacitance		C _{oss}		_	1260	K	
Switching time	Rise time	tr	$V_{GS}^{10} V$		5		ns
	Turn-ON time	t _{on}			20	_	
	Fall time	t _f	VDD ≃ 30	$\mathbb{N}_{\mathcal{A}}$	15		
	Turn-OFF time	toff	Duty \leq 1%, t _w = 10 μ s	/	96		
Total gate charge (gate-source plus gate-drain)		Qg	$V_{\text{DD}} \simeq 60 \text{ V}, \text{ V}_{\text{GS}} = 5 \text{ V}, \text{ I}_{\text{D}} = 60 \text{ A}$		48		
			$V_{DD} \simeq 60 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 60 \text{ A}$	_	86	_	
Gate-source charge 1		Qgs1		_	16	_	nC
Gate-drain ("miller") charge		Qgd	$V_{DD} \simeq 60 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 60 \text{ A}$	_	20	_	
Gate switch charge		Ø\$w		_	27	—	

Source-Drain Ratings and Characteristics (Ta = 25° C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	> -	_	_	60	Α
Pulse drain reverse current (Note 1)	IDRP	_	_	_	240	Α
Forward voltage (diode)	VDSF	I _{DR} = 60 A, V _{GS} = 0 V	_	-0.9	-1.2	V
Reverse recovery time	tr	$I_{DR} = 60 \text{ A}, V_{GS} = 0 \text{ V},$	_	63	—	ns
Reverse recovery charge	Qrr	dI _{DR} /dt = 50 A/µs	_	63	_	nC

Marking

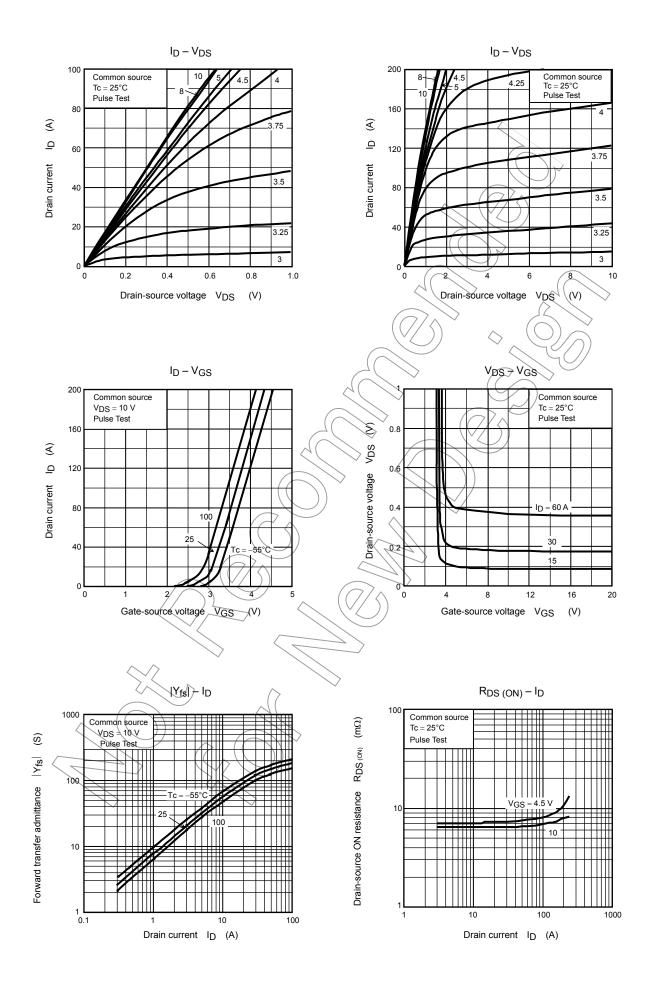


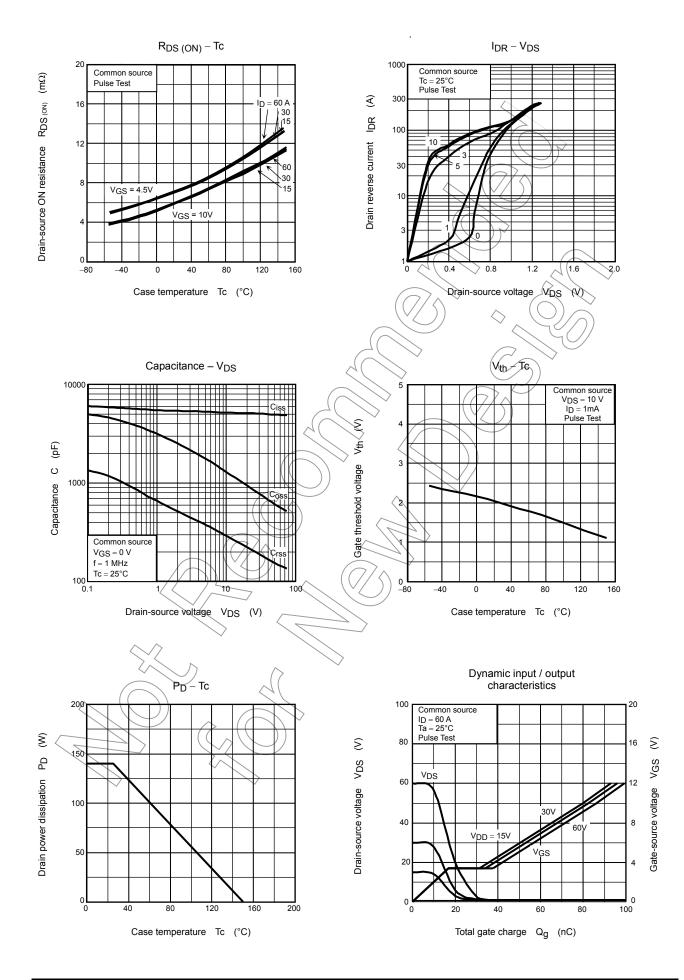
Note 4: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV

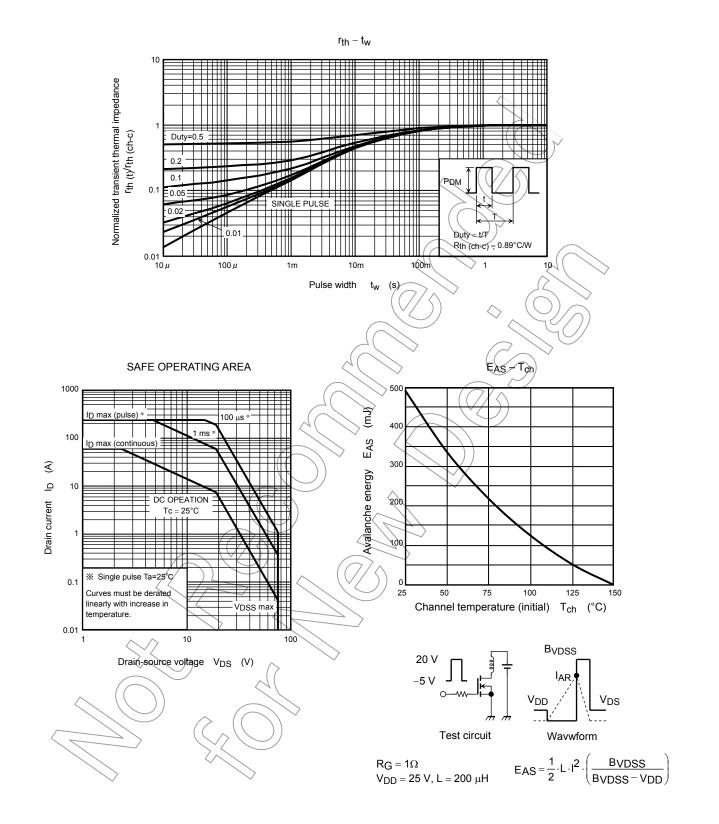
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

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